

EAST - [default.wsp:1]

File View Edit Tools Window Help

Pending
Active
L2: (1) (complementary near3 (data adj line)) same (equ
L3: (9) ((complementary near3 (data adj line)) same (eq
Failed
Saved
Favorites
Tagged (0)
UDC
Queue

USPAT; US-PGPUB; EPO; JPO
Default operator: OR
Highlight all hit terms initially

	Type	L #	Hits	Search Text	DBs
1	BRS	L2	1	((complementary near3 (data adj line)) same (equalizer or equalization) same precharge same region same third	USPAT; US-PGPUB; EPO; JPO
2	BRS	L3	9	((complementary near3 (data adj line)) same (equalizer or equalization)) and precharge and region and third	USPAT; US-PGPUB; EPO; JPO

Start 10:57

EAST - [default.wsp:1]

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☐ Pending
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☐ Failed
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☐ Queue

DBs: USPAT, US-PGPUB, EPO, JPO
 Default operator: OR
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((complementary near3 (data adj line)) same (equalizer or equalization)) and precharge and region and third

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XR
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20040037123 A1	20040226	19	Integrated circuit devices including equalization/precharge circuits for improving signal transmission	365/200	
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20030151966 A1	20030814	25	High speed DRAM architecture with uniform access latency	365/222	
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20020027810 A1	20020307	19	Semiconductor integrated circuit	365/189.11	
4	<input type="checkbox"/>	<input type="checkbox"/>	US 6493282 B2	20021210	20	Semiconductor integrated circuit	365/226	365/189.09; 365/203
5	<input type="checkbox"/>	<input type="checkbox"/>	US 6275070 B1	20010814	13	Integrated circuit having a high speed clock input buffer	326/98	326/62; 326/68; 326/80;
6	<input type="checkbox"/>	<input type="checkbox"/>	US 6097648 A	20000801	14	Semiconductor memory device having plurality of equalizer control line drivers	365/203	365/230.06
7	<input type="checkbox"/>	<input type="checkbox"/>	US 4941128 A	19900710	23	Semiconductor memory device having means for providing a precharge voltage equivalent to a prescribed selection voltage	365/203	365/190; 365/207; 365/230.01
8	<input type="checkbox"/>	<input type="checkbox"/>	US 4893278 A	19900109	19	Semiconductor memory device including precharge/equalization circuitry for the complementary data lines	365/203	365/190
9	<input type="checkbox"/>	<input type="checkbox"/>	US 4682200 A	19870721	20	Semiconductor memory device with matched equivalent series resistances to the complementary data lines	365/190	257/382; 257/401; 257/527.008

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